

FIG.1

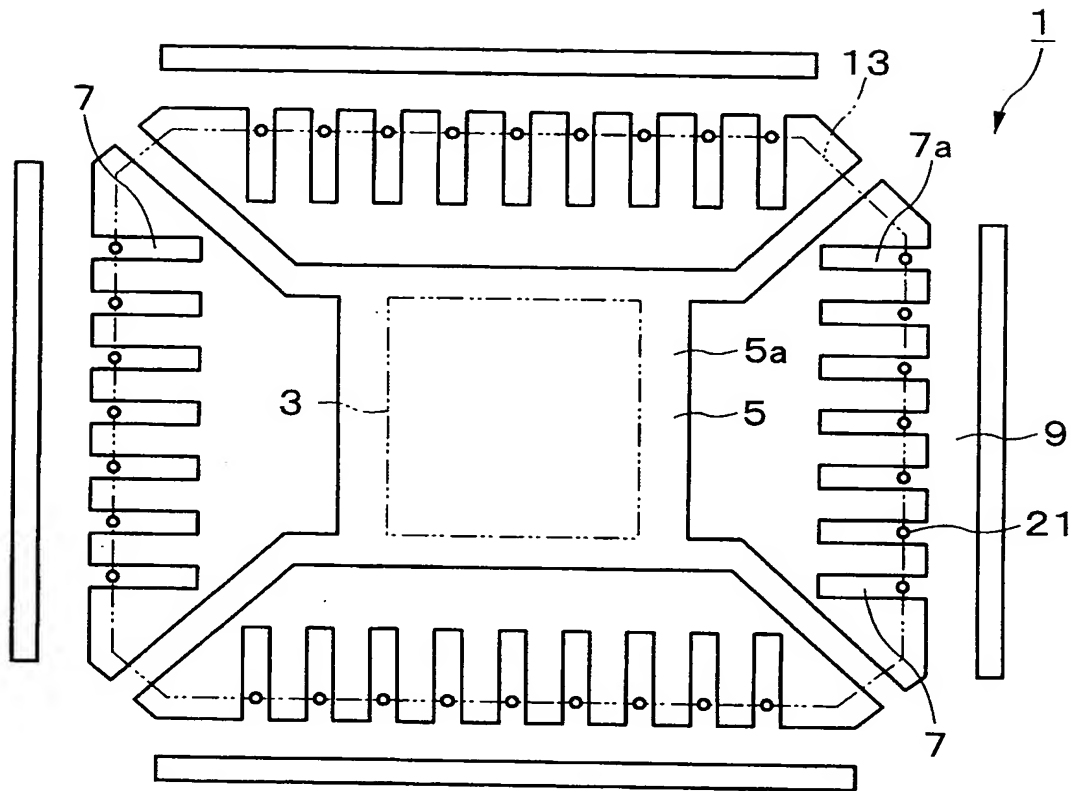


FIG.2

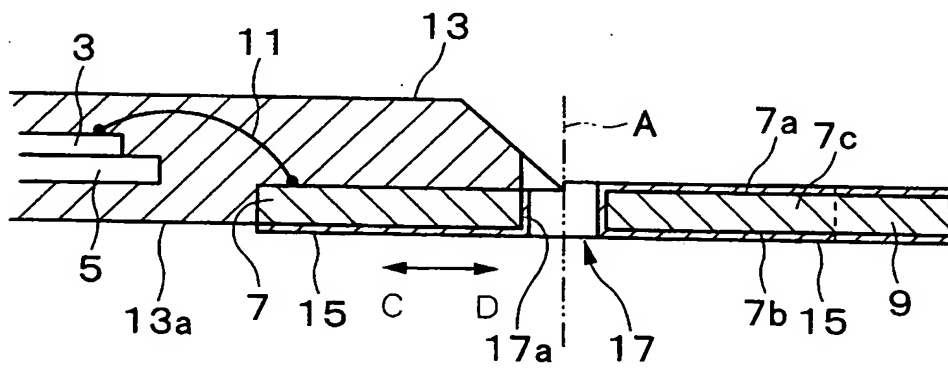


FIG.3A

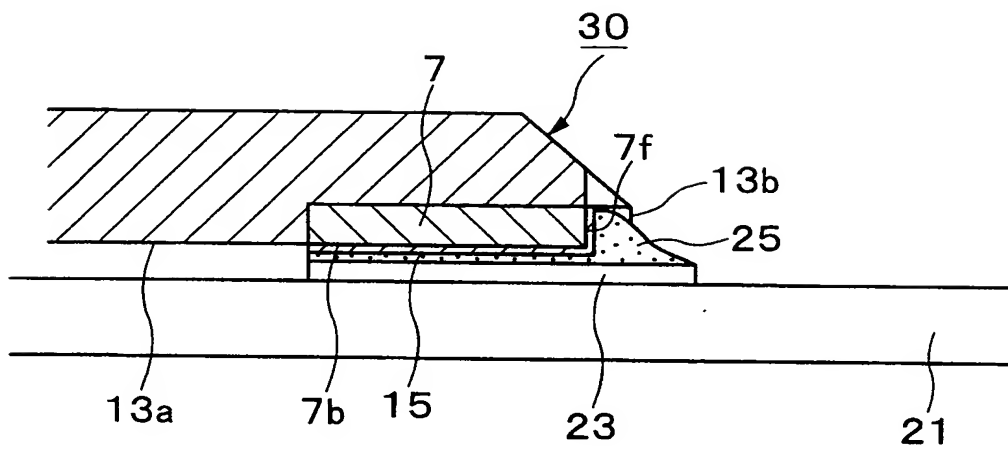
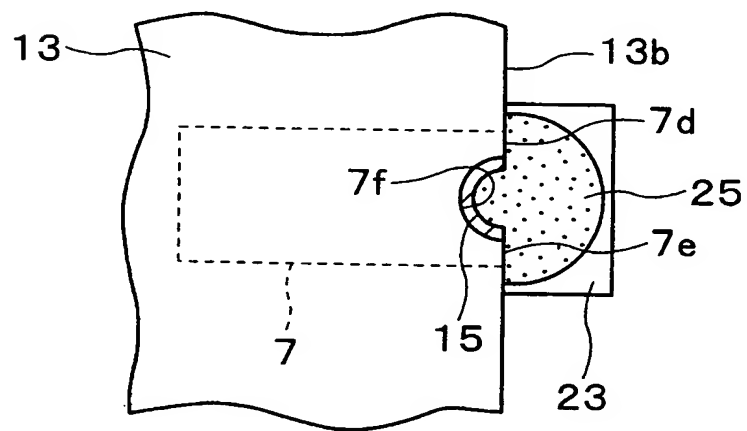


FIG.3B



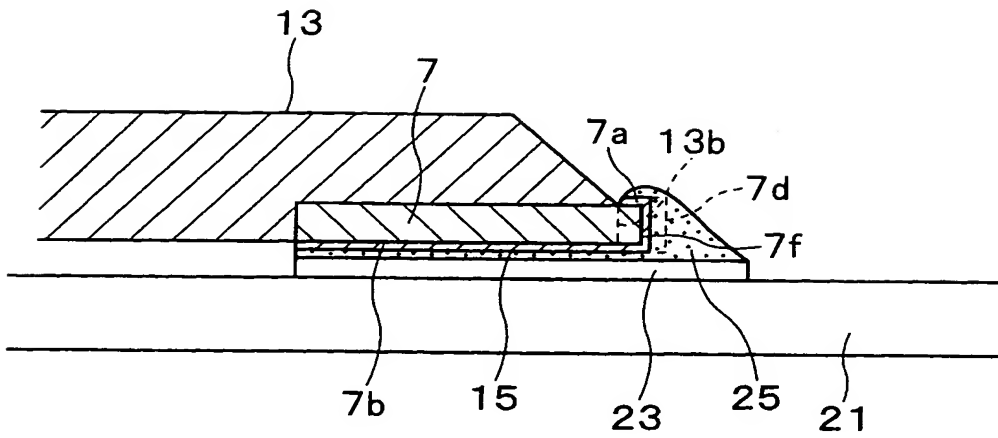
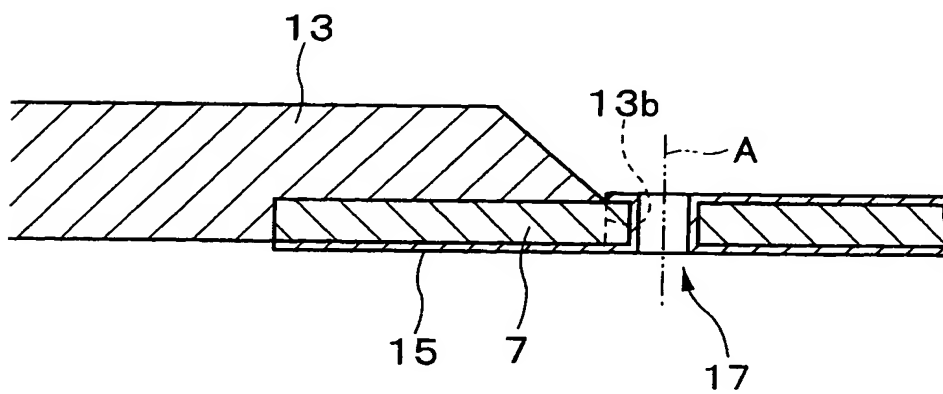


Figure 1 is a cross-sectional view of a semiconductor device. It shows a substrate 13 with a layer 15 on top. A structure 7 is formed on the layer 15. A dashed line 13b indicates a boundary within the substrate 13. A vertical dashed line 17 is shown, and a label A points to a specific region of the device.



This diagram shows a cross-sectional view of a semiconductor device. It features a substrate with a series of rectangular structures. The first three structures are identical, each consisting of a base layer (6) and a top layer (15). The fourth structure is more complex, featuring a base layer (6) and a top layer (6a) with a patterned surface (6b) and a central region (6d) filled with a stippled material. A sloped surface (31) is formed on the right side of the device, and a dashed line (13) indicates a boundary or interface.

FIG.8

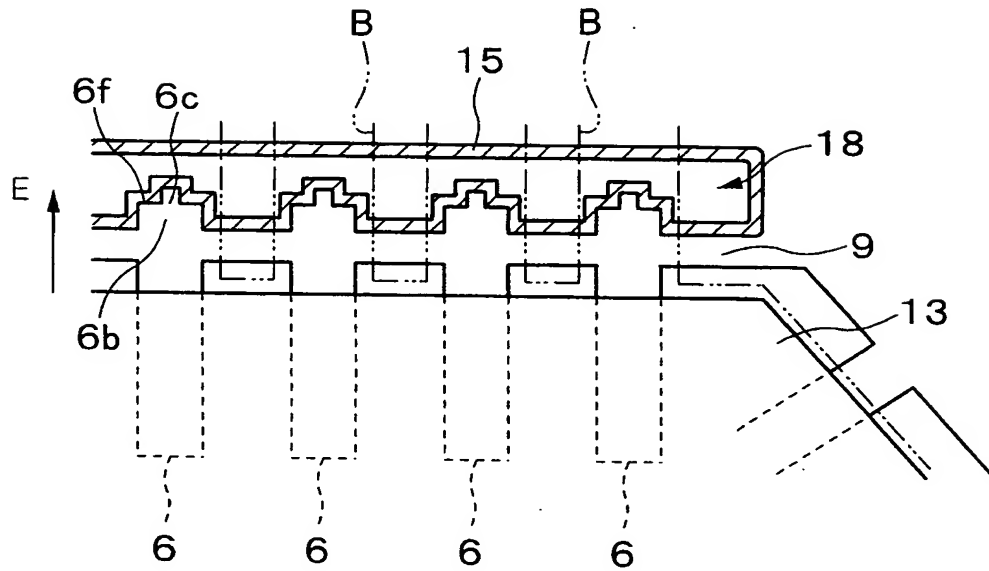


FIG.9

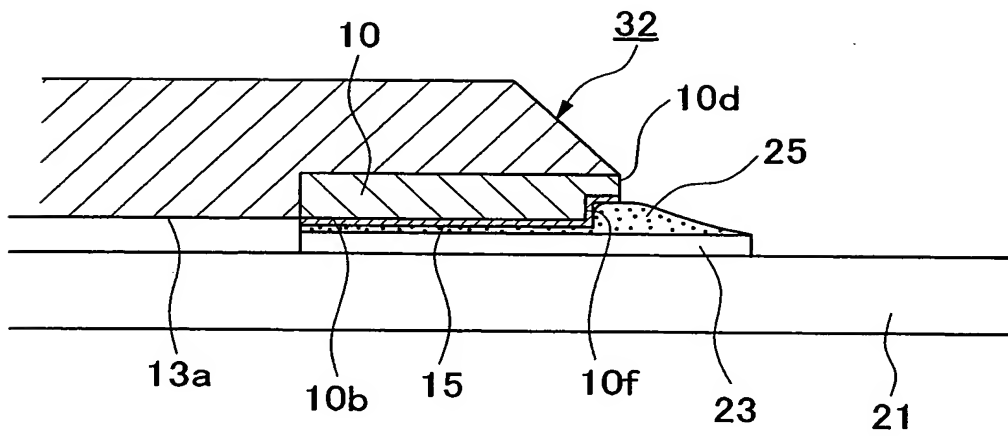


FIG.10

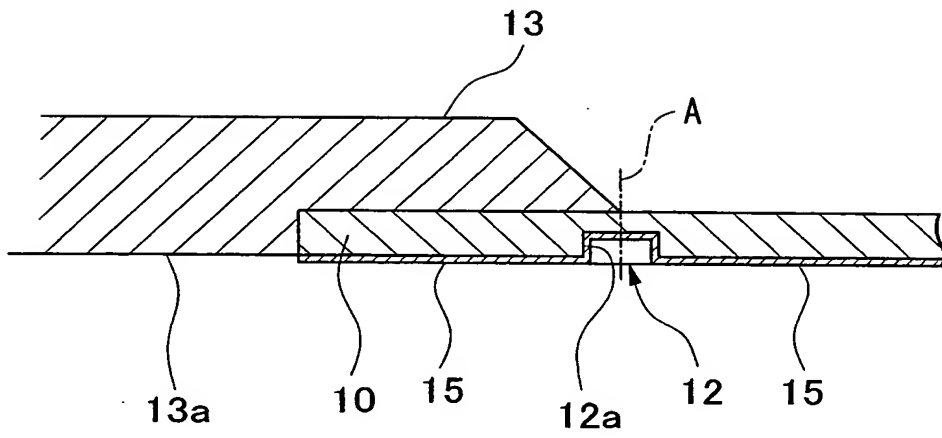
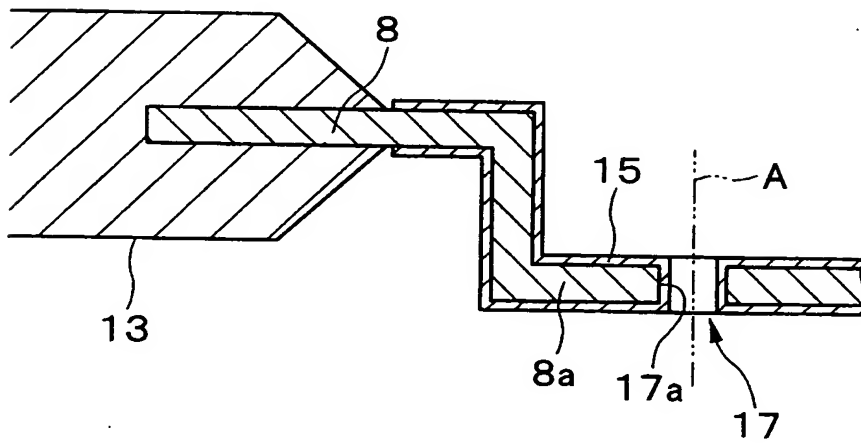


FIG.11



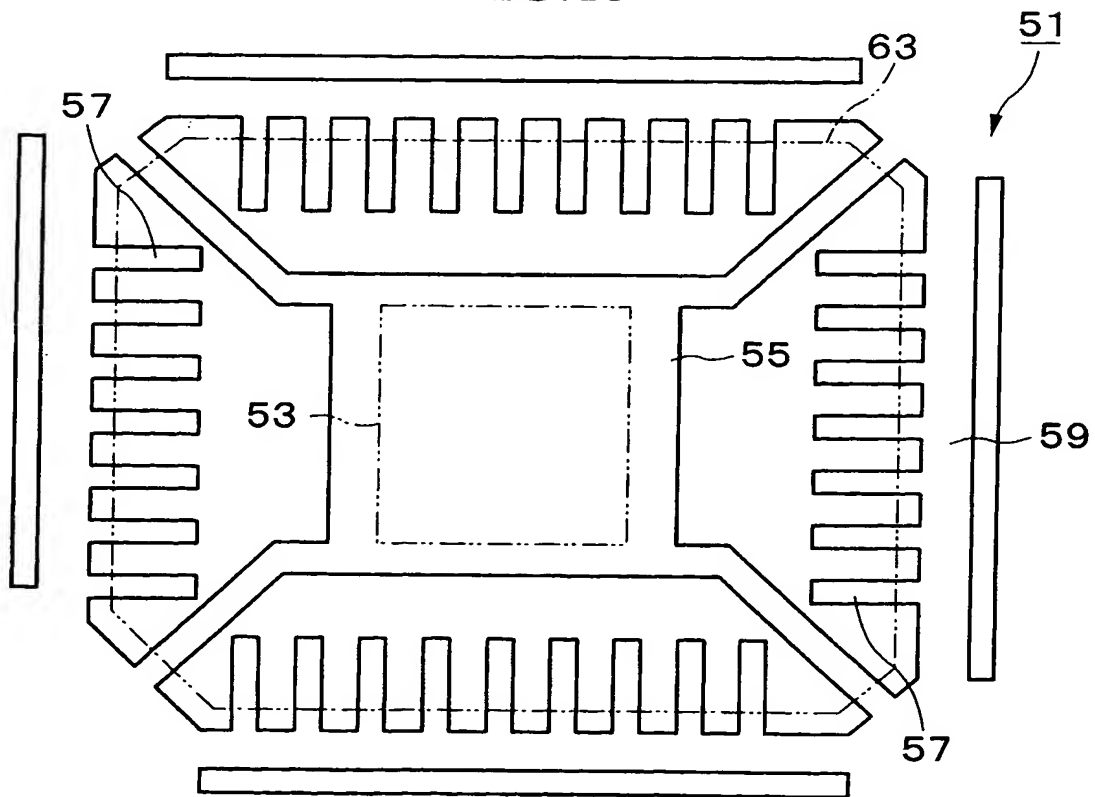


FIG.14

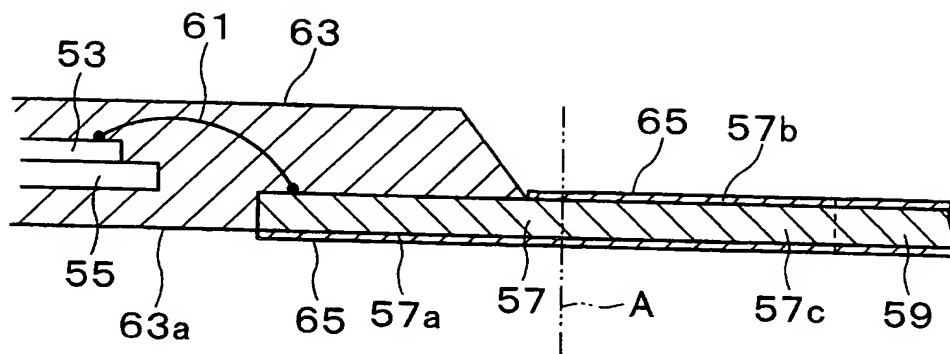


FIG.15

